

IN THE SPECIFICATION:

Please replace paragraph [0031] with the following amended paragraph:

[0031] Still referring to Figure 1, a substrate 114 is disposed on the substrate support 130 which may be a polishing head used in a chemical mechanical planarization process as shown. The substrate support 130 typically applies a pressure in the range of about 0.1 psi to about 6 psi to the substrate surface to be electrochemically and mechanically polished. On the substrate support 130, the substrate 114 is exposed to the electrolyte composition 220 and contacted with the second electrode 207. A bias from a power source 200 is then applied to both electrodes 204 and 207. The bias typically ranges from about -15 volts to about 15 volts. In one aspect, the positive bias ranges from about 0.1 volts to about 10 volts and the negative bias ranges from about -0.1 to about -10 volts. Alternatively, the bias may be a current density between about 0.01 and about 40 milliamps/cm² for a 200 mm substrate. The bias may be varied in power and application depending upon the user requirements in removing material from the substrate surface. The bias may also be applied by an electrical pulse modulation technique, which applies a constant current density or voltage for a first time period, then applies a constant reverse current density or voltage for a second time period, and repeats the first and second steps, as is described in co-pending U.S. Patent Application, serial no. 09/450,937, entitled "Method And Apparatus For Electrochemical Mechanical Planarization", filed on November 29, 1999, now U.S. Patent No. 6,379,223 which is incorporated by reference herein.